The following classification changes will be effected by this Notice of Changes:

<table>
<thead>
<tr>
<th>Action*</th>
<th>Subclass</th>
<th>Group(s)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Symbols deleted:</td>
<td>H01L</td>
<td>29/784</td>
</tr>
<tr>
<td></td>
<td>H01L</td>
<td>29/804</td>
</tr>
<tr>
<td>New symbols:</td>
<td>H01L</td>
<td>29/78391</td>
</tr>
<tr>
<td></td>
<td>H01L</td>
<td>29/803</td>
</tr>
<tr>
<td>Title Change:</td>
<td>H01L</td>
<td>29/778</td>
</tr>
<tr>
<td></td>
<td>H01L</td>
<td>29/788</td>
</tr>
</tbody>
</table>

This Notice of Changes includes the following [Check the ones included]:

1. CLASSIFICATION SCHEME CHANGES
   - A. New, Deleted, and Modified group(s)
   - B. New, Deleted, and Modified Warning Notice(s)
   - C. New, Deleted, and Modified Note(s)
2. DEFINITIONS
3. REVISION CONCORDANCE LIST (RCL)
4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)
5. CROSS-REFERENCE LIST (CRL)
### 1. CLASSIFICATION SCHEME CHANGES

#### A. New, Deleted, and Modified group(s)

**SUBCLASS H01L - SEMICONDUCTOR DEVICES; ELECTRIC SOLID STATE DEVICES NOT OTHERWISE PROVIDED FOR**

<table>
<thead>
<tr>
<th>Type</th>
<th>Symbol</th>
<th>Intent Level</th>
<th>Title</th>
</tr>
</thead>
<tbody>
<tr>
<td>M</td>
<td>29/778</td>
<td>4</td>
<td>with two-dimensional charge carrier gas channel, e.g. HEMT; { with two-dimensional charge-carrier layer formed at a heterojunction interface (H01L29/803 takes precedence) }</td>
</tr>
<tr>
<td>U</td>
<td>29/7839</td>
<td>6</td>
<td>{ with Schottky drain or source contact }</td>
</tr>
<tr>
<td>N</td>
<td>29/78391</td>
<td>6</td>
<td>{the gate comprising a layer which is used for its ferroelectric properties}</td>
</tr>
<tr>
<td>D</td>
<td>29/784</td>
<td>6</td>
<td>&lt; administrative transfer to H01L29/78391 &gt;</td>
</tr>
<tr>
<td>M</td>
<td>29/788</td>
<td>6</td>
<td>with floating gate { (H01L29/78391 takes precedence) }</td>
</tr>
<tr>
<td>U</td>
<td>29/802</td>
<td>6</td>
<td>{ with heterojunction gate, e.g. transistors with semiconductor layer acting as gate insulating layer, MIS-like transistors (H01L 29/806 takes precedence; with one dimensional electron gas H01L 29/775; with dimensional electron gas H01L 29/778) }</td>
</tr>
<tr>
<td>N</td>
<td>29/803</td>
<td>7</td>
<td>[Programmable transistors, e.g. with charge-trapping quantum well]</td>
</tr>
<tr>
<td>D</td>
<td>29/804</td>
<td>7</td>
<td>&lt; administrative transfer to H01L29/803 &gt;</td>
</tr>
</tbody>
</table>

*N = new entries, C = entries with modified file scope, M = subclasses or groups do not impact the file scope, D = deleted entries, U = entries that are unchanged, but presented in order to show the hierarchy of the scheme to simplify understanding*
2. Deleted and Modified Definitions

SUBCLASS H01L - SEMICONDUCTOR DEVICES; ELECTRIC SOLID STATE DEVICES NOT OTHERWISE PROVIDED FOR

<table>
<thead>
<tr>
<th>Type</th>
<th>In the Definition of</th>
<th>Specific Location</th>
<th>Old</th>
<th>Action</th>
</tr>
</thead>
<tbody>
<tr>
<td>M</td>
<td>H01L27/11585</td>
<td>Informative reference</td>
<td>H01L29/784</td>
<td>Change to H01L29/78391</td>
</tr>
</tbody>
</table>

*M = modified definition;  D = deleted definition

**H01L27/11585**

[N: with gate electrode comprising a layer which is used for its ferroelectric memory properties, e.g. MFS (metalferroelectric-\semiconductor), MFMIS (metal-ferroelectricmetal-insulator-semiconductor)]

**Informative references**

Attention is drawn to the following places, which may be of interest for search:

| Memory transistors with a ferroelectric layer in the gate stack per se | H01L29/78391 |
3. REVISION CONCORDANCE LIST (RCL)

<table>
<thead>
<tr>
<th>From CPC Symbol</th>
<th>To CPC Symbol</th>
</tr>
</thead>
<tbody>
<tr>
<td>H01L 29/784</td>
<td>H01L29/78391</td>
</tr>
<tr>
<td>H01L 29/804</td>
<td>H01L29/803</td>
</tr>
</tbody>
</table>
4. CHANGES TO THE CPC-TO-IPC CONCORDANCE LIST (CICL)

<table>
<thead>
<tr>
<th>CPC</th>
<th>IPC</th>
<th>Action</th>
</tr>
</thead>
<tbody>
<tr>
<td>H01L 29/784</td>
<td></td>
<td>Delete entire entry</td>
</tr>
<tr>
<td>H01L 29/804</td>
<td></td>
<td>Delete entire entry</td>
</tr>
<tr>
<td>H01L 29/78391</td>
<td>H01L 29/78</td>
<td>Add</td>
</tr>
<tr>
<td>H01L 29/803</td>
<td>H01L 29/80</td>
<td>Add</td>
</tr>
</tbody>
</table>
5. CHANGES TO THE CROSS REFERENCE LIST (CRL)

Scheme references impacted by this revision project

<table>
<thead>
<tr>
<th>Location of reference to be changed</th>
<th>Referenced subclass or group to be changed</th>
<th>Changed to</th>
</tr>
</thead>
<tbody>
<tr>
<td>H01L 29/778</td>
<td>H01L 29/804</td>
<td>H01L 29/803</td>
</tr>
<tr>
<td>H01L 29/788</td>
<td>H01L 29/784</td>
<td>H01L 29/78391</td>
</tr>
</tbody>
</table>

Definitions references impacted by this revision project

<table>
<thead>
<tr>
<th>Location of reference to be changed</th>
<th>Referenced subclass or group to be changed</th>
<th>Section of definition</th>
<th>Changed to</th>
</tr>
</thead>
<tbody>
<tr>
<td>H01L 27/11585</td>
<td>H01L29/784</td>
<td>Informative references</td>
<td>H01L29/78391</td>
</tr>
</tbody>
</table>